



US006559424B2

(12) **United States Patent**
O'Carroll et al.

(10) **Patent No.:** **US 6,559,424 B2**
(45) **Date of Patent:** **May 6, 2003**

(54) **WINDOWS USED IN THERMAL PROCESSING CHAMBERS**
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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 206 days.

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(21) Appl. No.: **09/753,216**

(22) Filed: **Jan. 2, 2001**

(65) **Prior Publication Data**

US 2002/0084424 A1 Jul. 4, 2002

(51) **Int. Cl.**⁷ **F27B 5/14**

(52) **U.S. Cl.** **219/390**; 219/405; 219/411; 392/416; 392/418; 118/724; 118/50.1

(58) **Field of Search** 219/390, 405, 219/411; 392/416, 418; 118/724, 725, 50.1

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(57) **ABSTRACT**

An apparatus for heat treating semiconductor wafers in a thermal processing chamber using light energy is provided. In one embodiment, the apparatus contains a window located between the semiconductor wafer and the energy source. The window contains a member that defines at least one passage capable of being placed into communication with a coolant to cool the window and at least partially offset the "first wafer effect". Additionally, in some embodiments, the window has a thickness greater than about 1 inch so that it can withstand pressures applied during wafer processing.

41 Claims, 8 Drawing Sheets

